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BUK7880-55A

N-channel TrenchMOS standard level FET

19 June 2015 **Product data sheet**

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP General Purpose Automotive (GPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

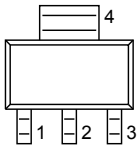
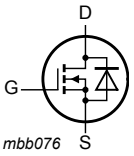
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 150$ °C		-	-	55	V
I_D	drain current	V_{GS} = 10 V; T_{sp} = 25 °C; Fig. 2; Fig. 3		-	-	7	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; Fig. 1		-	-	8	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 9; Fig. 10		-	68	80	mΩ
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 7 A; $V_{sup} \leq 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	53	mJ

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SC-73 (SOT223)	
2	D	drain		
3	S	source		
4	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7880-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BUK7880-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7880-55A	788055A
BUK7880-55A/CU	788055

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 150$ °C		-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	55	V
V_{GS}	gate-source voltage			-20	20	V
P_{tot}	total power dissipation	T_{sp} = 25 °C; Fig. 1		-	8	W
I_D	drain current	T_{sp} = 100 °C; V_{GS} = 10 V; Fig. 2		-	5	A
		T_{sp} = 25 °C; V_{GS} = 10 V; Fig. 2; Fig. 3		-	7	A
I_{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \leq 10$ µs; Fig. 3		-	30	A

Symbol	Parameter	Conditions		Min	Max	Unit
T_{stg}	storage temperature			-55	150	°C
T_j	junction temperature			-55	150	°C
Source-drain diode						
I_S	source current	T_{sp} = 25 °C		-	7	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{sp} = 25 °C		-	30	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 7 A; $V_{sup} \leq 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	53	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	Fig. 4	[1][2][3][4]	-		J

[1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.
[3] Repetitive avalanche rating limited by an average junction temperature of 150 °C
[4] Refer to application note AN10273 for further information.

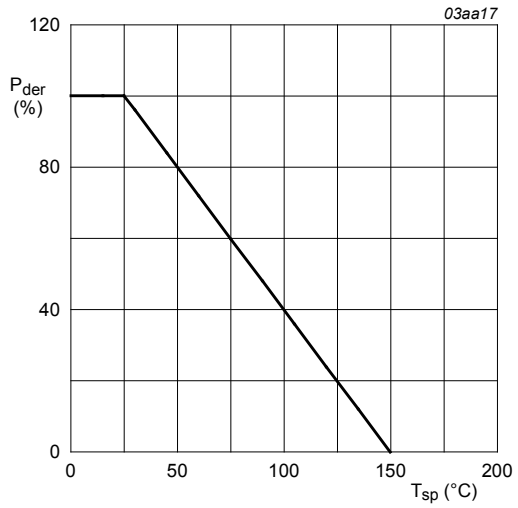


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

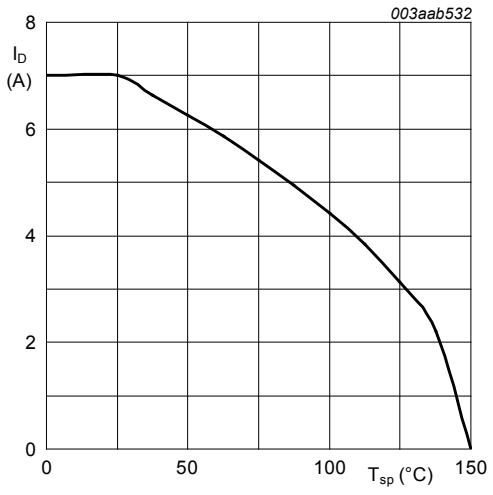


Fig. 2. Continuous drain current as a function of solder point temperature

$$V_{GS} \geq 10\,V$$

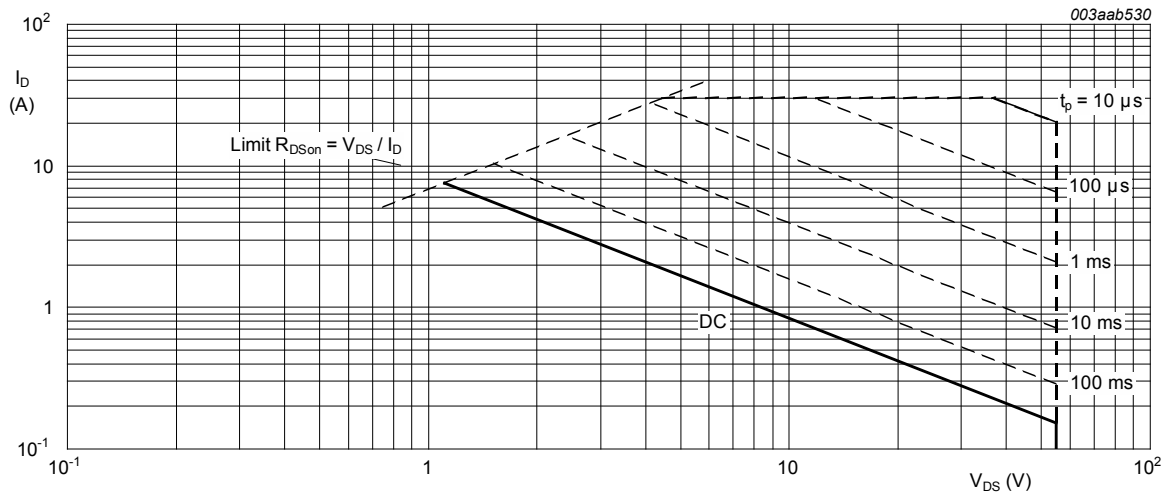


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{sp} = 25\ °C; I_{DM}$ is single pulse

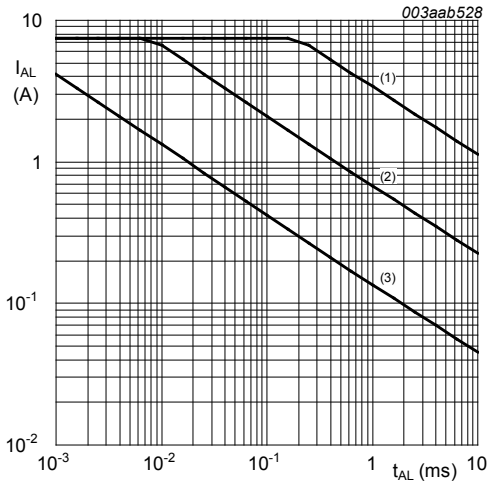


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

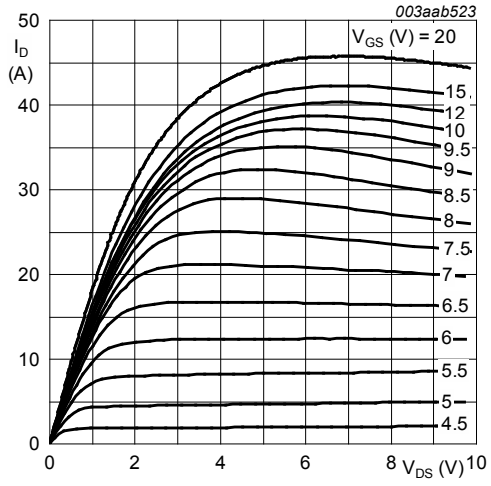
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient			-	120	-	K/W

10. Characteristics

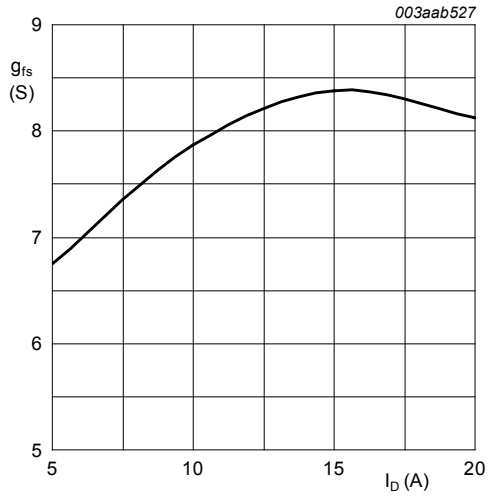
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		55	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 8		2	3	4	V
V_{GSth}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 8		-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 150 °C; Fig. 8		1.2	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C		-	0.05	10	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 150 °C; Fig. 9; Fig. 10		-	-	148	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 9; Fig. 10		-	68	80	mΩ
I_{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 150 °C		-	-	500	µA
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 10 A; V_{DS} = 44 V; V_{GS} = 10 V; Fig. 11		-	12	-	nC
Q_{GS}	gate-source charge			-	2.5	-	nC
Q_{GD}	gate-drain charge			-	5	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 12		-	374	500	pF
C_{oss}	output capacitance			-	92	110	pF
C_{rss}	reverse transfer capacitance			-	62	85	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω		-	8	-	ns
t_r	rise time			-	52	-	ns
$t_{d(off)}$	turn-off delay time			-	17	-	ns
t_f	fall time			-	9	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 15 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 13		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V		-	33	-	ns
Q_r	recovered charge			-	31	-	nC



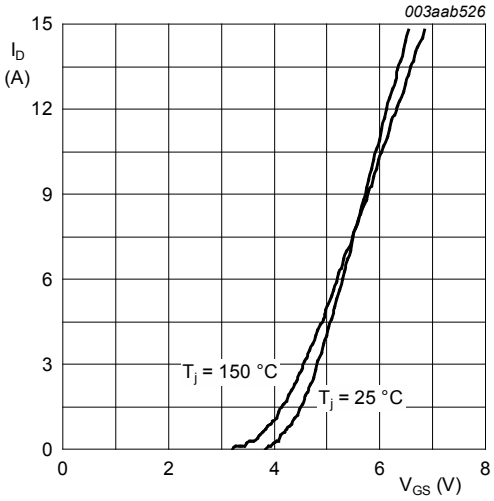
T_j = 25 °C

Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



T_j = 25 °C; V_{DS} = 15 V

Fig. 6. Forward transconductance as a function of drain current; typical values



V_{DS} = 15 V

Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

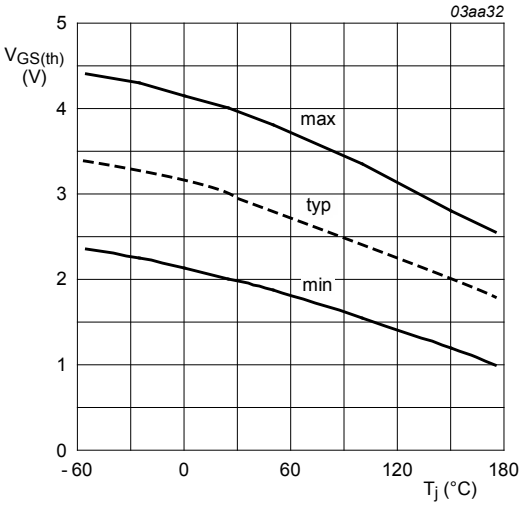


Fig. 8. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

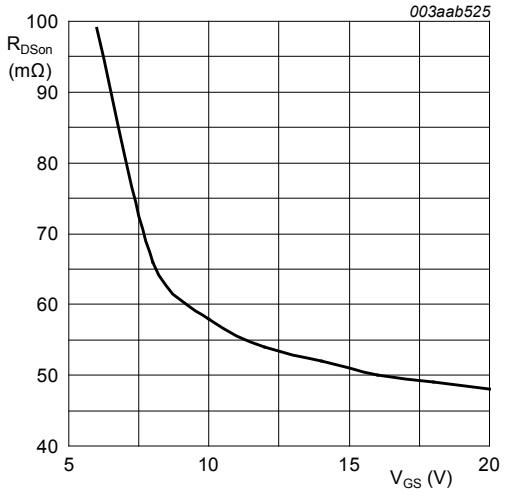


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25\,°C; I_D = 10\,A$$

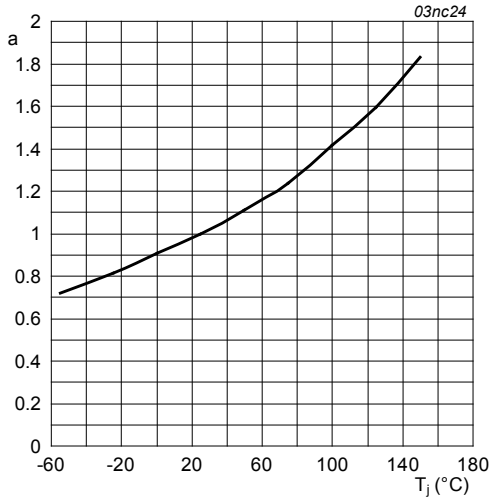


Fig. 10. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

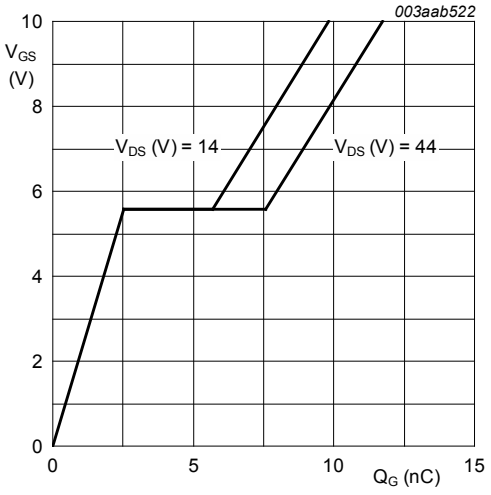


Fig. 11. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\,°C; I_D = 10A$$

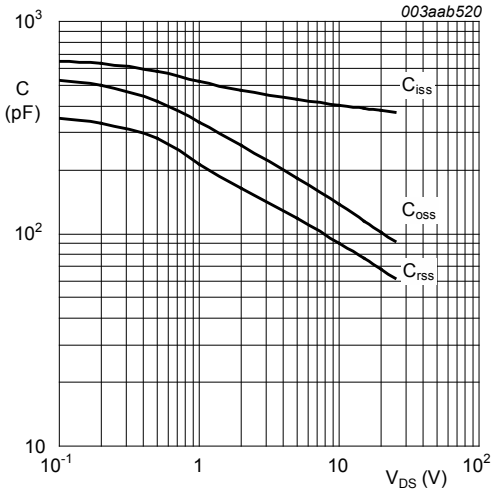


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

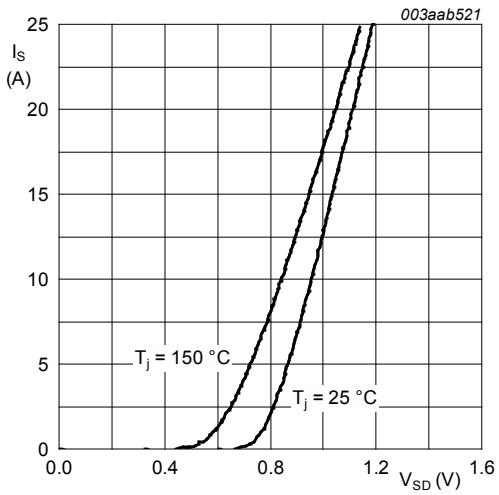
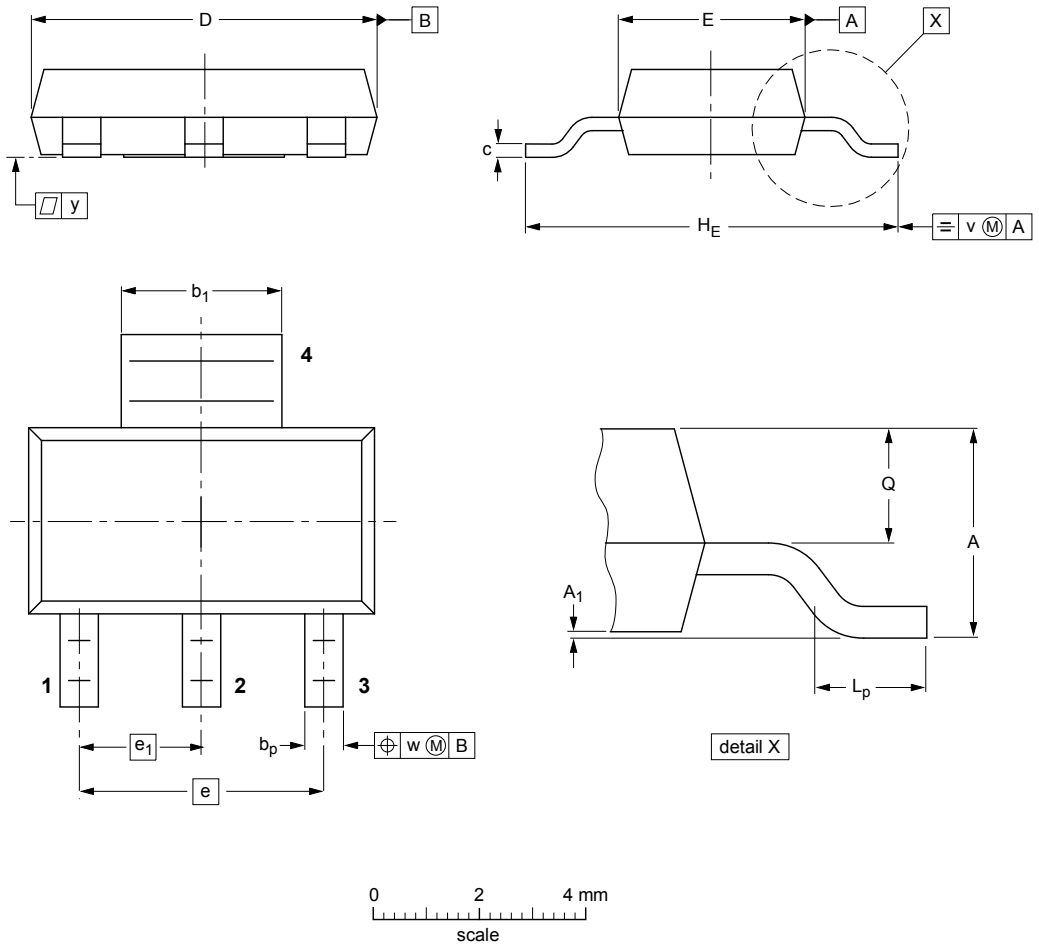


Fig. 13. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			~~04-11-10~~ 06-03-16

Fig. 14. Package outline SC-73 (SOT223)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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